

- Page 31, line 14, change "Figure" to --Fig.--; and
line 28, change "Figure" to --Fig.--.
- Page 35, line 7, change "high energy" to --the high energy source--.
- Page 36, line 21, change "layer" to --laser--.
- Page 41, line 8, change "TFT" to --a TFT--.
- Page 44, line 23, delete "on".
- Page 45, line 1, change "batter" to --battery--.
- Page 46, line 6, change "gammer" to --gamma--; and
line 23, change "Figure" to --Fig.--.
- Page 47, line 4, change "Figure" to --Fig.--;
line 7, change "Figure" to --Fig.--;
line 21, change "Figure" to --Fig.--;
line 26, change "Figure" to --Fig.--; and
line 27, change "Figure" to --Fig.--.
- Page 48, line 15, change "manufacture" to --the manufacture--.

IN THE DRAWINGS:

Applicants propose to amend Figs. 3 and 8 as shown in red in the marked sheets attached to the Request for Approval of Drawing Corrections submitted herewith.

IN THE CLAIMS:

Please cancel claim 3 without prejudice or disclaimer.

Please amend claims 1, 12, 20, 25, 30, 35, 40, 45, 46, 56 and 58 as follows:

1. (Twice Amended) A method of forming a crystalline film, comprising the steps of:
- forming a thin film having a surface on a substrate; and